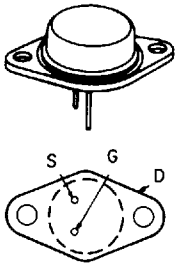



Power MOSFETS

| ECG Type | Description and Application | Transconductance gfs μ mhos | Drain to Source Breakdown Voltage BV _{DSS} | Gate to Source Breakdown Voltage BV _{GS} | Continuous Drain Current I _D Amps | Gate to Source Threshold Voltage V _{GS} (th) | Drain to Source Resistance ^r DS (on) Ohms | Input Cap C _{iss} pf | Device Dissipation @T _C =25° C P _D Watts | Package |
|---------------------------------|---|---------------------------------|---|---|--|---|--|-------------------------------|--|---|
| | | | | | | | | | | Case/Fig./Basing |
| ECG2392 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 6 Min | 100 Min | ±20 Max* | 32 | 4 Max | .06 Max | 1500 Max | 125 Max | TO-3 Fig. T28  ECG2392 use Fig. T28A |
| ECG2386 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 2 Min | 600 Min | ±20 Max* | 6 | 4.5 Max | 1.2 Max | 1800 Max | 150 Max | |
| ECG2384 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 1.8 Min | 800 Min | ±20 Max* | 6 | 4 Max | 1.5 Max | 3500 Max | 125 Max | |
| ECG2900 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 3 Min | 60 Min | ±20 Max* | 12 | 4.5 Max | .2 Max | 800 Max | 75 Max | TO-220 Fig. T41  |
| ECG2389 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 8 Min | 60 Min | ±30 Max* | 35 | 4 Max | .045 Max | 2000 Max | 125 Max | |
| ECG2395 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 17 Min | 60 Min | ±30 Max* | 50 | 4 Max | .028 Max | 2000 Max | 150 Max | |
| ECG2382 ▲ (Compl to ECG2383) | MOSFET, N-Ch, Enhancement Hi Speed Switch | 1.5 Min | 100 Min | ±20 Max* | 8 | 4 Max | .5 Max | 750 Max | 75 Max | |
| ECG2383 ▲ (Compl to ECG2382) | MOSFET, P-Ch, Enhancement Hi Speed Switch | 2 Min | 100 Min | ±20 Max* | 8 | 4.5 Max | .4 Max | 1200 Max | 75 Max | |
| ECG66 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 3 Min | 100 Min | ±20 Max* | 12 | 4.5 Max | .18 Max | 1200 Max | 75 Max | |
| ECG2371 ▲ | MOSFET, P-Ch, Enhancement Hi Speed Switch | 6 Min | 100 Min | ±20 max* | 19 | 4 Max | .2 Max | 1400 Typ | 150 Max | |
| ECG2396 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 12 Min | 100 Min | ±30 Max* | 30 | 4 Max | .057 Max | 2000 Max | 150 Max | |
| ECG2372 ▲ | MOSFET, P-Ch, Enhancement Hi Speed Switch | 1 Min | 200 Min | ±20 Max* | 3.5 | 4 Max | 1.5 Max | 350 Typ | 40 Max | |
| ECG2373 ▲ | MOSFET P-Ch Enhancement Hi Speed Switch | 4 Min | 200 Min | ±20 max* | 11 | 4 Max | .5 Max | 1200 Typ | 125 Max | |

* Warning - Exceeding BV_{GS} maximum will result in permanent damage to the gate region oxide layer.
 ▲ Refer to MOSFET Handling Precautions - Page 1-34

Package Outlines - See Page 1-91